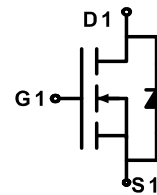


AP6324

N-Channel Enhancement Mosfet

Feature

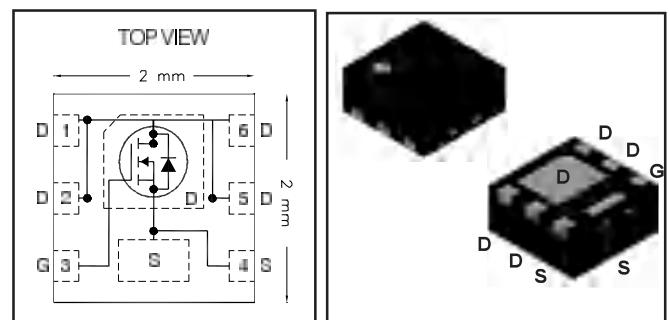
- 30V,5.8A
 $R_{DS(ON)} < 26m\Omega @ V_{GS}=10V$ TYP=18 m Ω
 $R_{DS(ON)} < 32m\Omega @ V_{GS}=4.5V$ TYP=23 m Ω
- Advanced Trench Technology
- Lead free product is acquired



Schematic diagram

Application

- Interfacing Switching
- Load Switching
- Power management



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
6324	AP6324	PDFN2*2	7 inch	-	-

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a=25^\circ\text{C}$)	I_D	5.8	A
Continuous Drain Current ($T_a=70^\circ\text{C}$)	I_D	3.8	A
Pulsed Drain Current	I_{DM}	23	A
Power Dissipation	P_D	1.47	W
Thermal Resistance from Junction to Ambient ⁽⁴⁾	$R_{\theta JA}$	85	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage ⁽³⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.5	2.5	V
Drain-source on-resistance ⁽³⁾	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5.8A$	-	18	26	m Ω
		$V_{GS} = 4.5V, I_D = 3A$	-	23	32	
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	-	490	-	pF
Output Capacitance	C_{oss}		-	79	-	
Reverse Transfer Capacitance	C_{rss}		-	61	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15V, I_D = 3A,$ $V_{GS} = 4.5V, R_G = 10\Omega$	-	4.5	-	ns
Turn-on rise time	t_r		-	2.5	-	
Turn-off delay time	$t_{d(off)}$		-	14.5	-	
Turn-off fall time	t_f		-	3.5	-	
Total Gate Charge	Q_g	$V_{DS} = 15V, I_D = 5.8A,$ $V_{GS} = 4.5V$	-	5.2	-	nC
Gate-Source Charge	Q_{gs}		-	0.9	-	
Gate-Drain Charge	Q_{gd}		-	1.3	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$V_{GS} = 0V, I_S = 5.8A$	-	-	1.2	V
Diode Forward current ⁽⁴⁾	I_S		-	-	5.8	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. Surface Mounted on FR4 Board, $t_s \leq 10$ sec

Test Circuit

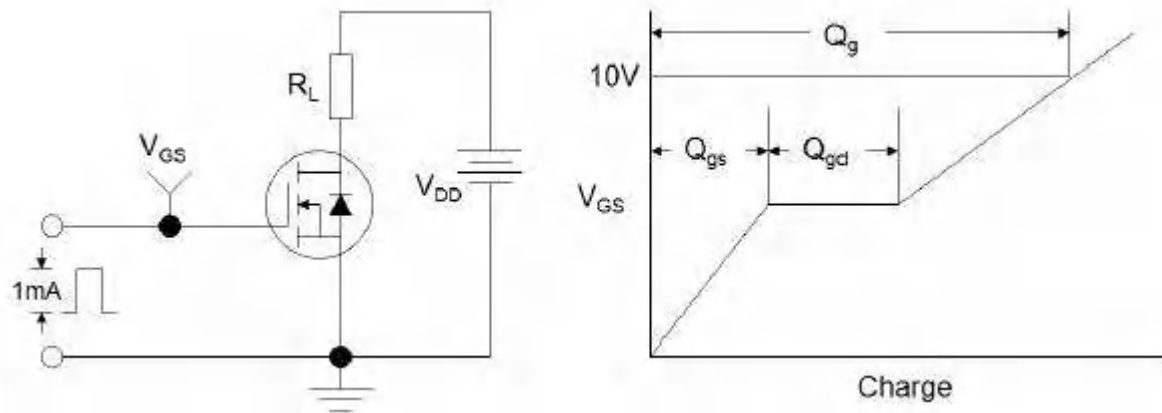


Figure1:Gate Charge Test Circuit & Waveform

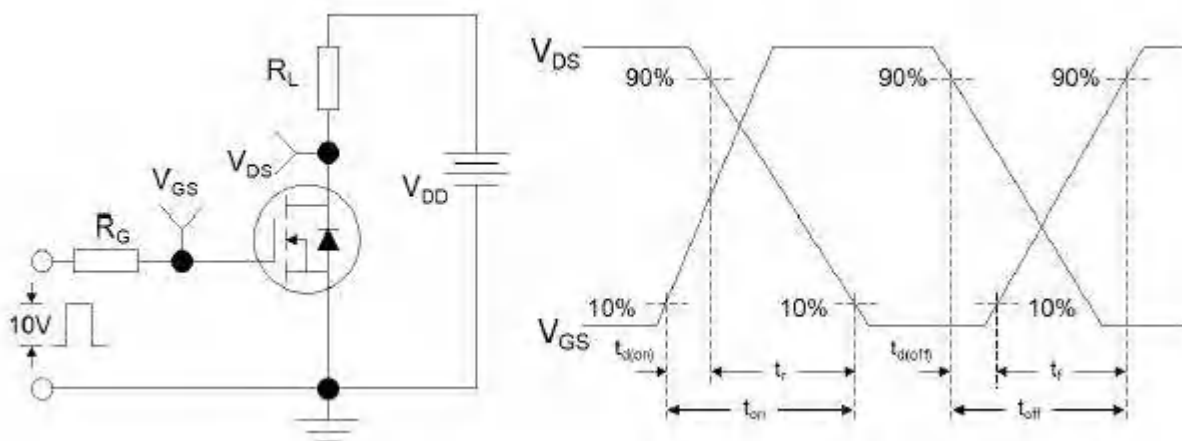


Figure 2: Resistive Switching Test Circuit & Waveforms

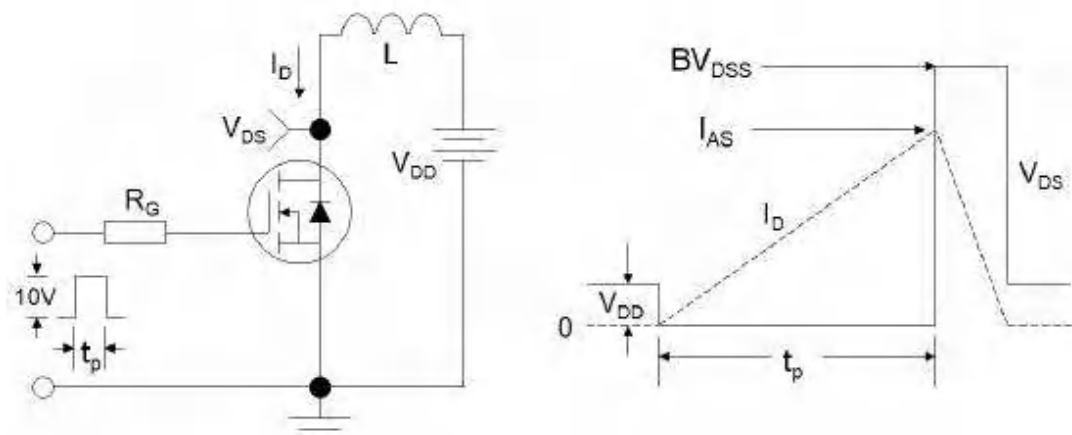


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Figure 1: Output Characteristics

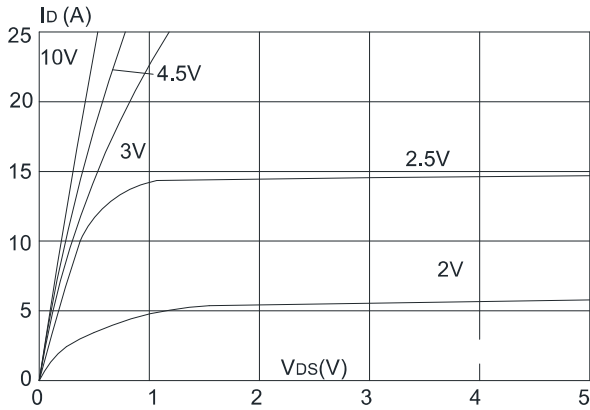


Figure 2: Typical Transfer Characteristics

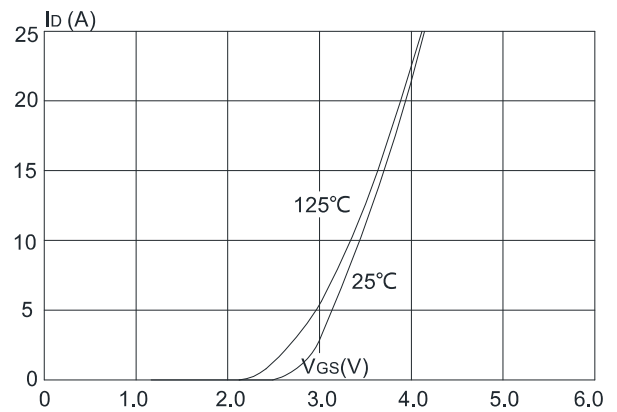


Figure 3: On-resistance vs. Drain Current

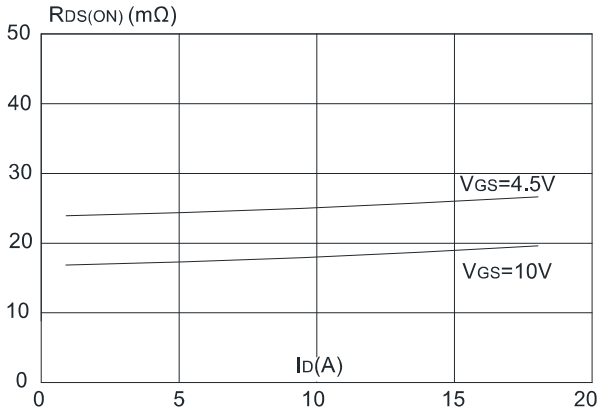


Figure 4: Body Diode Characteristics

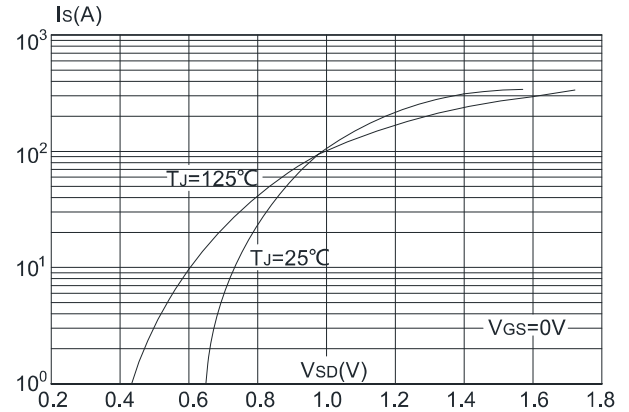


Figure 5: Gate Charge Characteristics

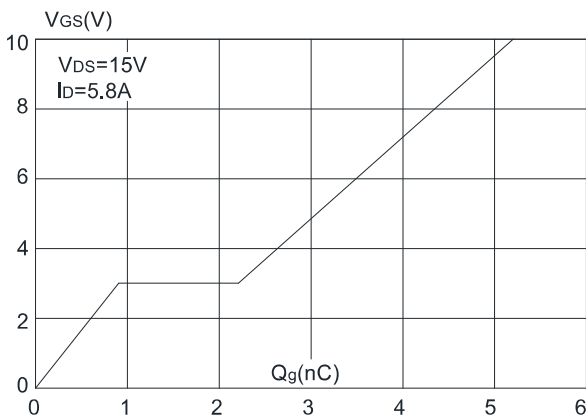


Figure 6: Capacitance Characteristics

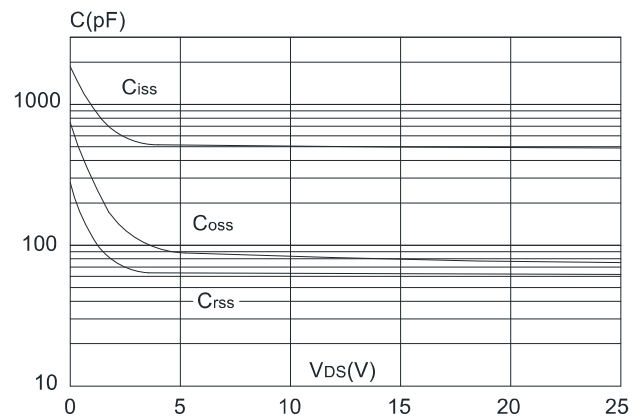


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

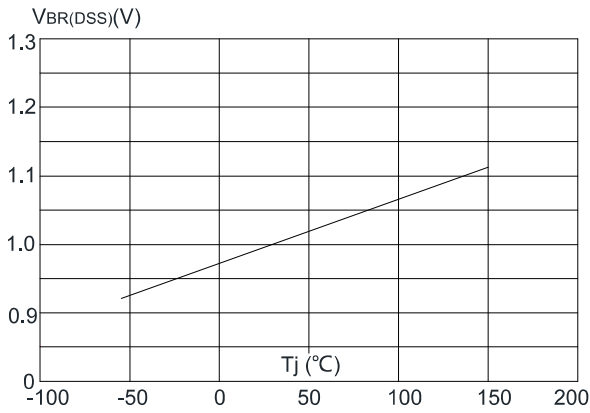


Figure 8: Normalized on Resistance vs. Junction Temperature

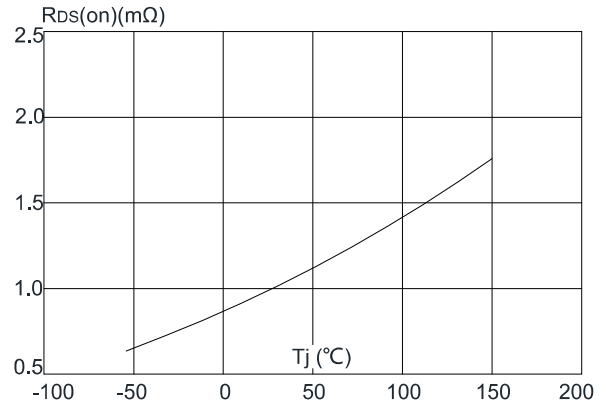


Figure 9: Maximum Safe Operating Area

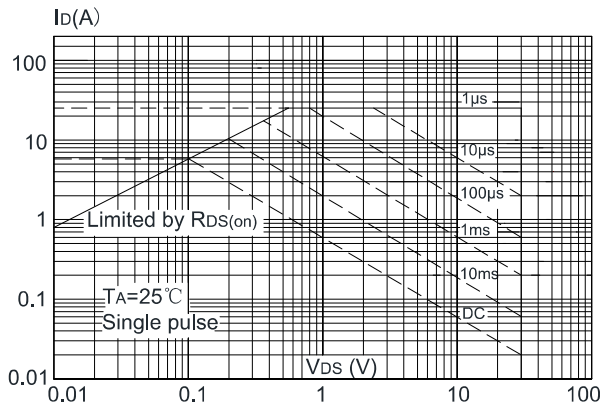


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

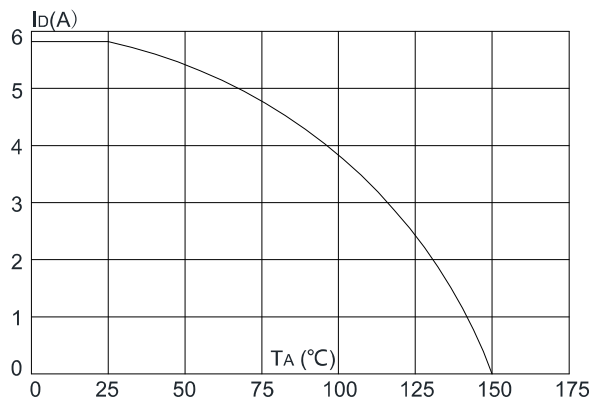
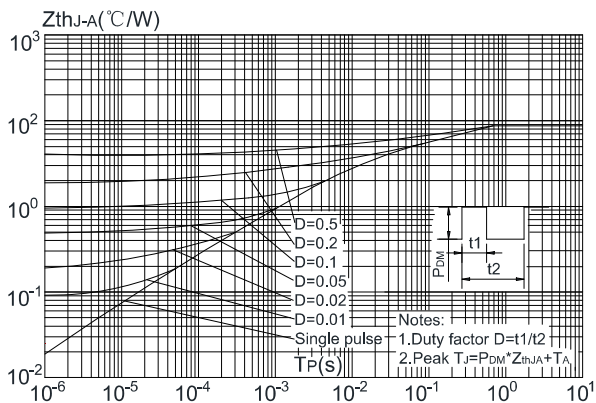
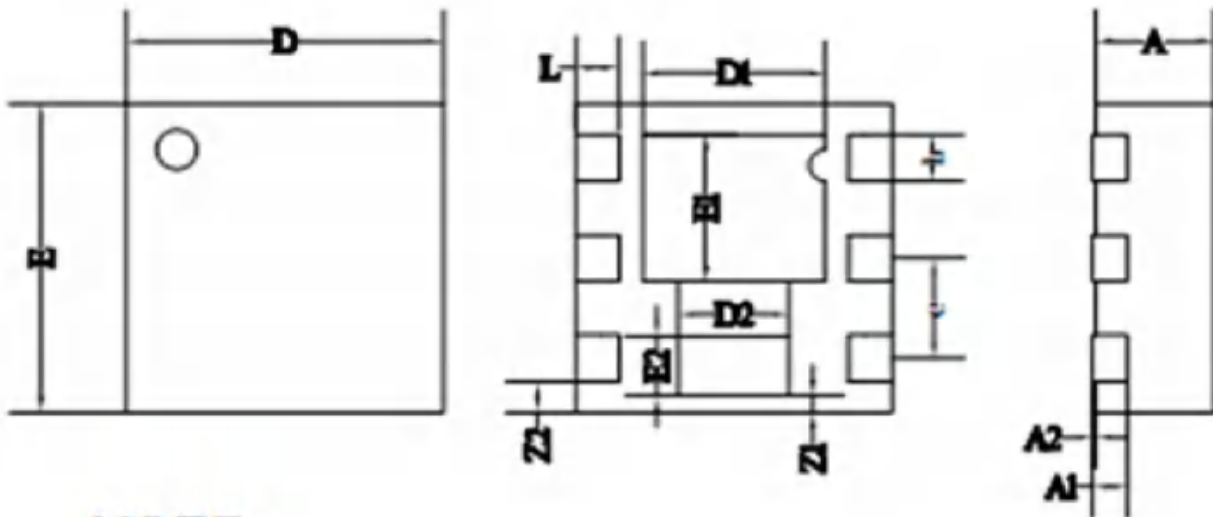


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Information



NOTE:
All dimensions are in mm

	MIN	NOM	MAX
D	1.95	2.00	2.05
E	1.95	2.00	2.05
D1	1.10	1.15	1.20
E1	0.90	0.95	1.00
D2	0.65	0.70	0.75
E2	0.33	0.38	0.43
L	0.23	0.275	0.33
b	0.25	0.30	0.35
e	0.65BSC		
A	0.45	0.50	0.55
A1	0.150REF		
A2	0.00	-	0.05
Z1	0.06	0.11	0.16
Z2	0.15	0.20	0.25